

**Features:**

- Broad band operation from 2.0 to 6.0 GHz
- Low VSWR, unconditional stable
- Small size, low cost
- SMA female connector I/O
- Single DC power supply, internal voltage regulator allowing operating voltage from +8V to +15V range
- Operating temperature -40~+75°C, storage temperature -55~+125°C

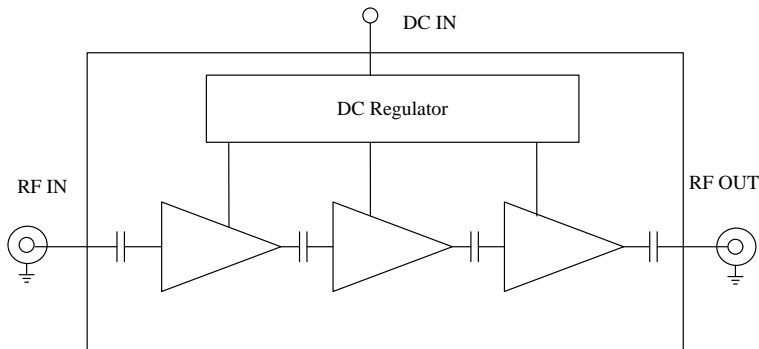
**General Description**

ABL0600-33-3509 is a three stage pHEMT transistor based broadband low noise amplifier module operating in the frequency of 2.0 to 6.0GHz. The amplifier provides 35dB of small signal gain with 0.9dB noise figure and excellent gain flatness, as well as good VSWR at both input and output. The amplifier requires only a positive DC power supply, its built-in DC voltage regulator allows for different DC voltage supply application.

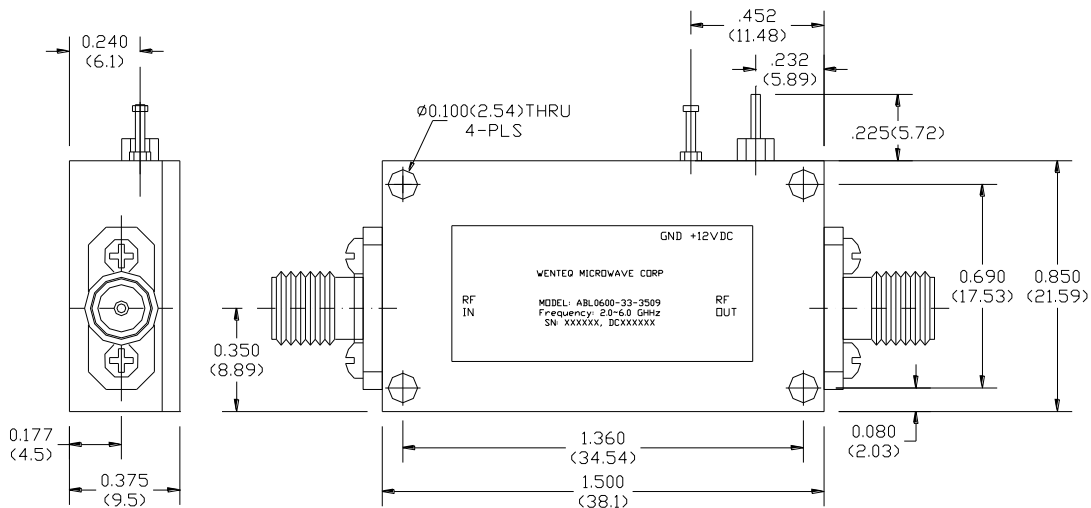
**Electrical Specifications**

Parameters	Units	Specifications		
		Minimum	Typical	Maximum
Frequency Range	MHz	2000		6000
Noise Figure @25°C	dB		0.9	1.10
Nominal SS Gain @25°C	dB	33.0	35.0	37.0
P-1dB Compression Point	dB	+12.0	+14.0	
Gain flatness	dB		+/-1.0	+/-1.25
Gain Variation over temperature	dB		+/-1.5	
Input VSWR	-		1.5:1	2.0:1
Output VSWR	-		1.6:1	2.0:1
Reverse Isolation	dB	55.0	60.0	
Spurious	dBc			-70.0
Operating Temperature	°C	-40.0		+75.0
Survival Temperature	°C	-55.0		+125.0
DC Voltage	V	+8.0	+12.0	+15.0
DC Supply Current	mA	80.0	90.0	110.0
RF In/Out connectors	-	SMA female		
DC Input Connector	-	Feed-thru PIN		
Size	inches	1.5×0.85×0.375		

Functional Diagram



Mechanical Structure:



Note: All units in inches.

Absolute Maximum Ratings

DC Voltage	+15V
RF Input Power	+10dBm
Storage Temperature	-55~+125°C
Operating Temperature	-40~+75°C



Electrostatic sensitive device, please observe precautions for handling this amplifier.